



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} -60 V
- I_D -100 A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) 8.8m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-6V$) 10m Ω
- 100% EAS Tested
- 100% V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- Excellent stability and uniformity



■ Electrical Characteristics ($T_J=25$ unless otherwise noted)





Typical Electrical and Thermal Characteristics Diagrams

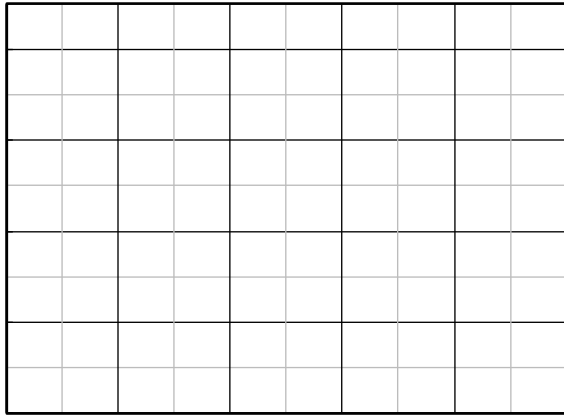


Figure 1. Output Characteristics

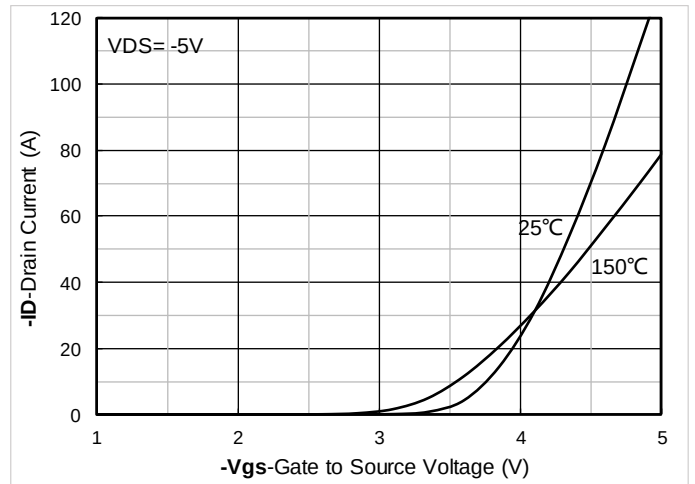


Figure 2. Transfer Characteristics

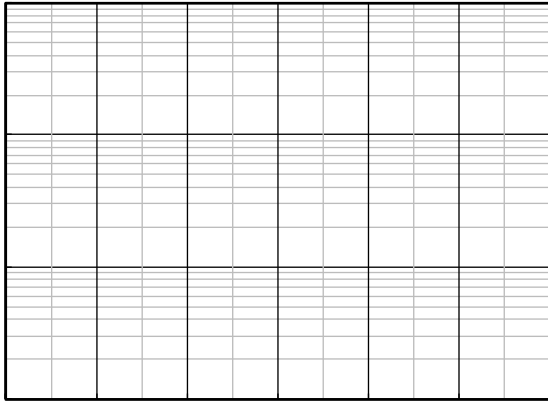


Figure 3. Capacitance Characteristics

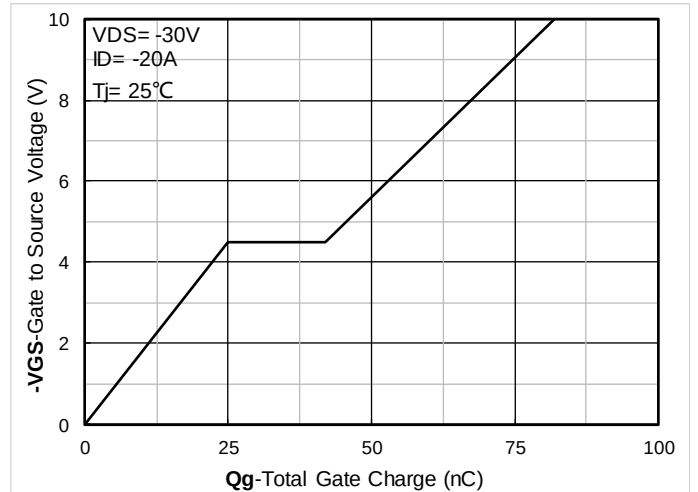


Figure 4. Gate Charge

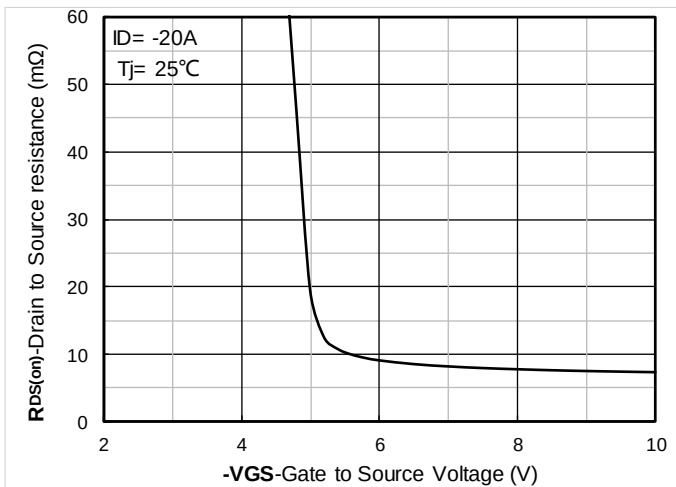


Figure 5. On-Resistance vs Gate to Source Voltage

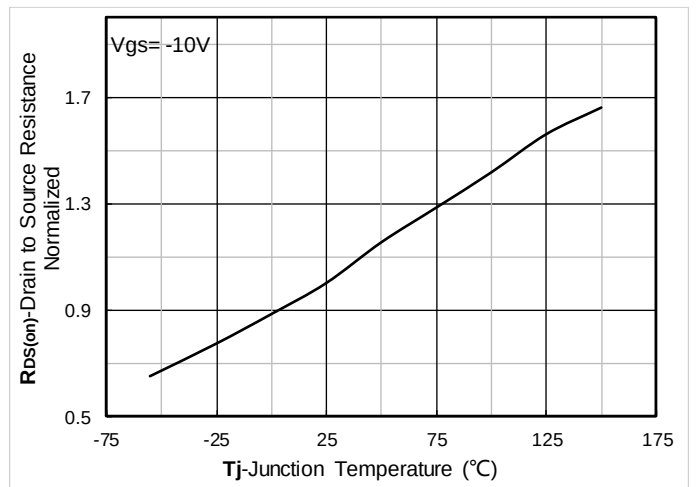


Figure 6. Normalized On-Resistance

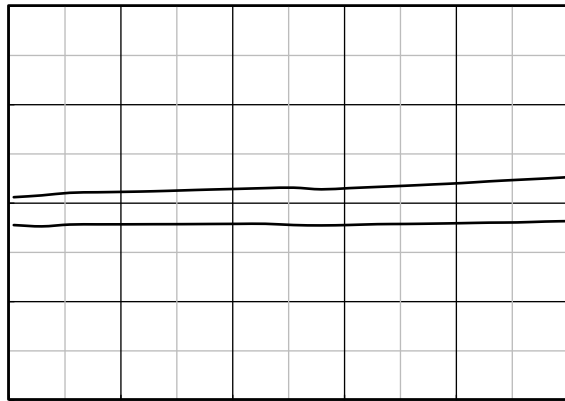


Figure 7. $R_{DS(on)}$ VS Drain Current

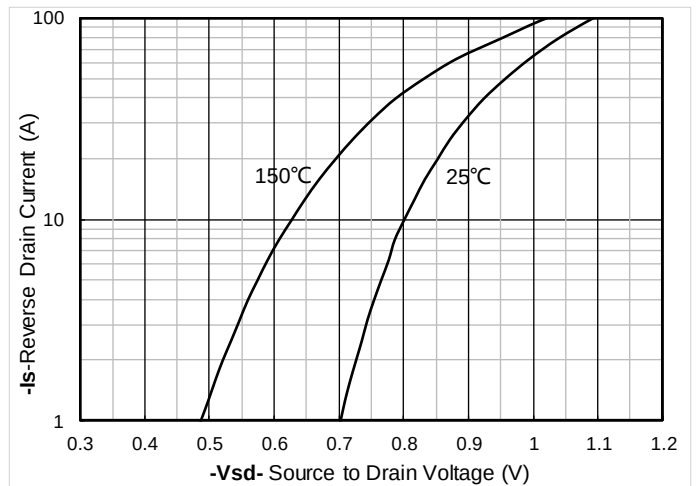


Figure 8. Forward characteristics of reverse diode

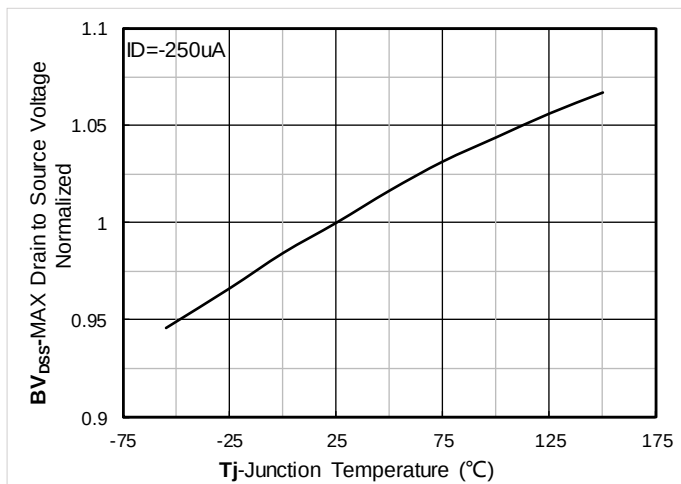


Figure 9. Normalized breakdown voltage

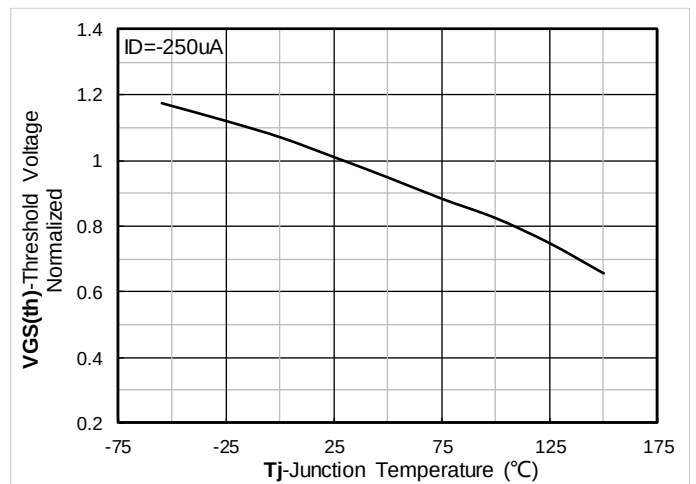


Figure 10. Normalized Threshold voltage

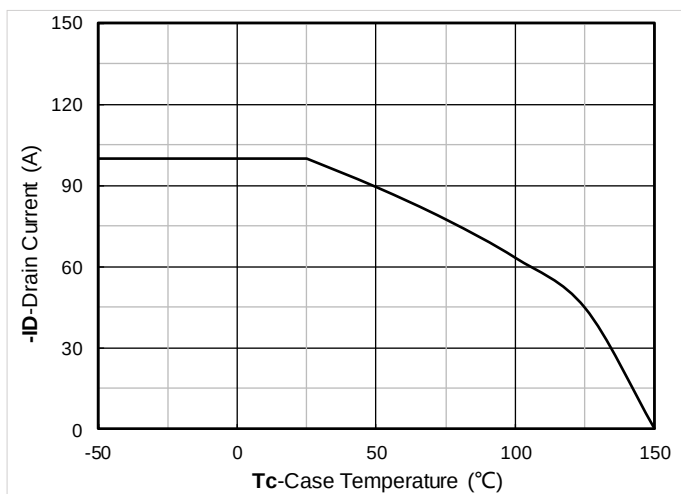


Figure 11. Current dissipation

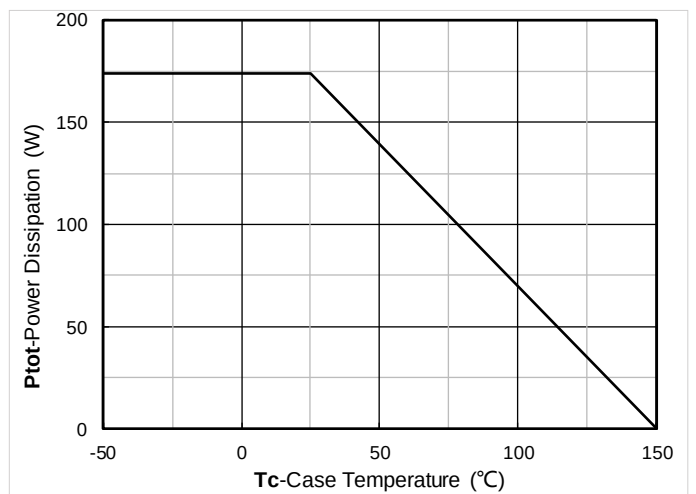


Figure 12. Power dissipation

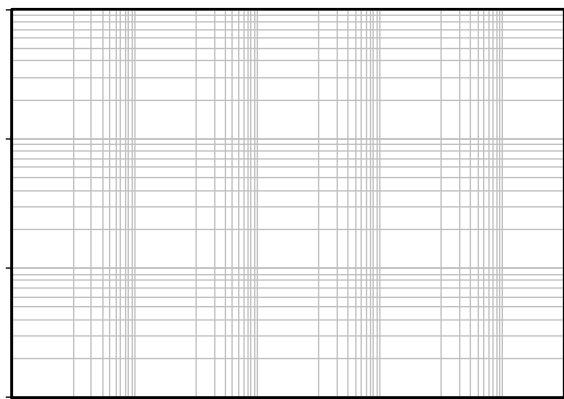


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



■TO



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on it 9 Tf1 0 0 1 32.64 654.94W*ⁿBT/ReS(o)-3(n)-3(e)-3()-41(o)9(n)-3()-41(i)-4(t 9 Tf1 0 0 1 32.64 654.94W*ⁿBT